

IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please REPLACE paragraph [0075] on pages 14 and 15 (which was previously replaced with amended paragraph [0075] on page 3 of the Amendment of September 29, 2005) with the following amended paragraph:

[0075] As described above, the active matrix display device according to the embodiments of the present invention have the following advantages. Since the source and drain electrodes directly contact the source and drain regions without contact holes, the number of mask processes is reduced, thereby simplifying a manufacturing process. Furthermore, since only five mask processes are required to manufacture the active matrix display device, the overall manufacturing process is simplified, leading to a higher manufacturing yield and a lower production cost. Also, since the capping layer is formed on the gate electrode of the TFT while an ion-implanting process is performed to form the low-density source and drain regions, damage to the gate electrode is prevented. In addition, due to the silicide layers respectively formed between the source and drain regions and the source and drain electrodes, a contact resistance is reduced, leading to a high reliability. In addition, since an LDD region or an off-set region is formed in a self-aligning manner through the spacers formed on both sidewall-side wall portions of the gate electrode and the capping layer, the manufacturing process is again simplified, and the electric characteristics such as an on/off current ratio are improved.